AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

Claims 1-17 (canceled).

18. (currently amended): A high-strength, low-temperature-sintered ceramic composition having a structure comprising ~~hexagonal~~ crystal phases of $SrAl_2Si_2O_8$, ~~and an~~ Al_2O_3, ~~crystal~~titanium oxide and silicon oxide, respectively, at least part of said crystal phase of $SrAl_2Si_2O_8$ determined by an X-ray diffraction measurement being composed of hexagonal $SrAl_2Si_2O_8$, said ceramic composition having a bending strength of 300 MPa or more.

19. (currently amended): ~~A~~The high-strength, low-temperature-sintered ceramic composition according to claim 18, comprising hexagonal $SrAl_2Si_2O_8$ in an Al_2O_3-SiO_2-SrO-based matrix, which contains an Al_2O_3 crystal ~~grains~~, a TiO_2 crystal and a SiO_2 crystal ~~and has a bending strength of 300 MPa or more~~.

20. (currently amended): The high-strength, low-temperature-sintered ceramic composition according to claim 19, wherein a part of said matrix is an amorphous phase~~, in which hexagonal $SrAl_2Si_2O_8$ is precipitated~~.

21. (canceled).

22. (currently amended): The high-strength, low-temperature-sintered ceramic composition according to claim 19, wherein said matrix ~~contains~~further comprises monoclinic $SrAl_2Si_2O_8$.

23. (currently amended): ~~A~~ The high-strength, low-temperature-sintered ceramic composition ~~having a structure comprising a $SrAl_2Si_2O_8$ crystal and an Al_2O_3 crystal~~according to claim 18, wherein said $SrAl_2Si_2O_8$ crystal being composed of hexagonal $SrAl_2Si_2O_8$ alone or hexagonal $SrAl_2Si_2O_8$ and monoclinic $SrAl_2Si_2O_8$, a peak intensity ratio represented by $I_{101} / (I_{101} + I_{002}) \times 100$ being 5% or more in an X-ray diffraction measurement by a Cu-Kα line, wherein I_{101} represents a peak intensity of a (101) plane of the hexagonal $SrAl_2Si_2O_8$, and I_{002} represents a peak intensity of a (002) plane of the monoclinic $SrAl_2Si_2O_8$~~, and said ceramic composition having a bending strength of 300 MPa or more~~.

24. (currently amended): The high-strength, low-temperature-sintered ceramic composition according to claim ~~23~~18, wherein said peak intensity ratio is 50% or more.

25. (currently amended): The high-strength, low-temperature-sintered ceramic composition according to claim ~~23~~18, ~~which has a structure comprising a matrix substantially composed of the $SrAl_2Si_2O_8$ crystal, which contains Al_2O_3 crystal grains, said $SrAl_2Si_2O_8$ crystal being composed of hexagonal $SrAl_2Si_2O_8$ alone or hexagonal $SrAl_2Si_2O_8$ and monoclinic $SrAl_2Si_2O_8$, and~~wherein a ~~percentage~~ ratio of said hexagonal $SrAl_2Si_2O_8$ in said $SrAl_2Si_2O_8$ crystal being 60% or more, and said ceramic composition having a bending strength of 400 MPa or more.

26. (currently amended): The high-strength, low-temperature-sintered ceramic composition according to claim 18, wherein said $A1_2O_3$ crystal ~~grams leave~~ is in the form of grains and said grains have an average diameter of 1 μm or less.

27. (currently amended): The high-strength, low-temperature-sintered ceramic composition according to claim 18, ~~wherein it comprises (a) 100% by mass of main components~~ comprising (a) 10-60% by mass of Al (as $A1_2O_3$), 25-60% by mass of Si (as SiO_2) and 7.5-50% by mass of Sr (as SrO), ~~(b) auxiliary components comprising at least one selected from the group consisting of 0.1-10% by mass of Bi (as Bi_2O_3), 0.1-5% by mass of Na (as Na_2O), 0.1-5% by mass, of K (as K_2O) and 0.1-5% by mass of Co (as CoO), and at least one selected from the group consisting of 0.01-5% by mass of Cu (as CuO), 0.01-5% by mass of Mn (as MnO_2), 0.01-5% by mass of Ag and 0.01-2% by mass of Zr (as ZrO_2),~~ and (c) inevitable impurities.

28. (currently amended): ~~The~~ A high-strength, low-temperature-sintered ceramic composition ~~according to claim 18~~having a structure comprising $SrA1_2Si_2O_8$ and Al_2O_3, said ceramic composition having a bending strength of 300 MPa or more, wherein it comprises (a) 100% by mass of main components comprising 10-60% by mass of Al (as $A1_2O_3$), 25-60% by mass of Si (as SiO_2), 7.5-50% by mass of Sr (as SrO) ~~and 20% or less by mass of Ti (as TiO_2)~~, (b) auxiliary components comprising at least one selected from the group consisting of 0.1-10% by mass of Bi (as Bi_2O_3), 0.1-5% by mass of Na (as Na_2O), 0.1-5% by mass of K (as K_2O) and 0.1-5% by mass of Co (as CoO), and at least one selected from the group consisting of 0.01-5% by mass of Cu (as CuO), 0.01-5% by mass of Mn (as MnO_2), 0.01-5% by mass of Ag and 0.01-2% by mass of Zr (as ZrO_2), and (c) inevitable impurities.

29. (currently amended): ~~The~~ A high-strength, low-temperature-sintered ceramic composition ~~according to claim 18~~having a structure comprising $SrAl_2Si_2O_8$ and Al_2O_3, said ceramic composition having a bending strength of 300 MPa or more, wherein it comprises (a) 100% by mass of main components comprising 10-60% by mass of Al (as Al_2O_3), 25-60% by mass of Si (as SiO_2), 7.5-50% by mass of Sr (as SrO) and 20% or less by mass of Ti (as TiO_2), (b) auxiliary components comprising at least one selected from the group consisting of 0.1-10% by mass of Bi (as Bi_2O_3), 0.1-5% by mass of Na (as Na_2O), 0.1-5% by mass of K as (K_2O) and 0.1-5% by mass of Co (as CoO), and at least one selected from the group consisting of 0.01-5% by mass of Cu (as CuO), 0.01-5% by mass of Mn (as MnO_2), 0.01-5% by mass of Ag and 0.01-2% by mass of Zr (as ZrO_2), and (c) inevitable impurities.

30. (currently amended): A method for producing the high-strength, low-temperature-sintered ceramic composition recited in ~~claim 18~~any one of claims 18-20 or 22-29, ~~by sintering~~comprising calcining ~~a ceramic green body comprising~~ aluminum oxide, silicon oxide and strontium oxide, or aluminum oxide, silicon oxide, strontium oxide and titanium oxide ~~as main starting materials,~~to obtain a calcined powder comprising a silicate glass containing Al_2O_3 and TiO_2, molding said calcined powder to a ceramic green body, followed by sintering said green body under such temperature and time conditions that a ratio of hexagonal $SrAl_2Si_2O_8$ in a $SrAl_2Si_2O_8$ crystal formed in a ceramic structure becomes 5% or more.

31. (previously presented): A laminated electronic part comprising pluralities of dielectric layers made of the high-strength, low-temperature-sintered ceramic composition

recited in claim 18, each of said dielectric layers being provided with a conductive pattern of a low-melting-point metal.

32. (previously presented): The laminated electronic part according to claim 31, wherein said low-melting-point metal is silver, copper, gold or an alloy thereof.

33. (previously presented): The laminated electronic part according to claim 31, wherein said conductive pattern constitutes an inductance element and/or a capacitance element.

34. (previously presented): The laminated electronic part according to claim 31, onto which at least one selected from the group consisting of an inductance element, a capacitance element, a switching element and a filter element is mounted.

35. (new): The high-strength, low-temperature-sintered ceramic composition according to claim 18, further comprising monoclinic $SrA1_2Si_2O_8$.

36. (new): A method for producing the high-strength, low-temperature-sintered ceramic composition recited in claim 35, comprising calcining aluminum oxide, silicon oxide and strontium oxide, or aluminum oxide, silicon oxide, strontium oxide and titanium oxide to obtain a calcined powder comprising a silicate glass containing $A1_2O_3$ and TiO_2, molding said calcined powder to a ceramic green body, followed by sintering said green body under such temperature and time conditions that a ratio of hexagonal $SrAl_2Si_2O_8$ in a $SrAl_2Si_2O_8$ crystal formed in a ceramic structure becomes 5% or more.